

**99-0222**

The invention relates to the semiconductor photography and can be utilized in holography, microelectronics, in the production of microfiches etc.

Summary of the invention: on the fine layer photosensitive structure  $SnO_2 - As_2Se_3 - Al$  is obtained an image by means of exposure. Simultaneously, an electric field is applied to the photosensitive structure, then it is effectuated the treatment in a solution containing, g/L:

anhydrous sodium carbonate	50
potassium chromate	1.5
distilled water	the rest.